

FORM PTO-1449 (SUBSTITUTE)

Attorney Docket No.:

Applic. No.

Z&PINFN10277

10/027,533

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))

Applicant

Walter Hartner et al.

Filing Date

Group Art Unit

December 26, 2001

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
BT	A	5,130,172	07/14/92	Hicks et al.			
	B	5,296,255	03/22/94	Gland et al.			
	C	5,320,978	06/14/94	Hsu			
	D	5,403,620	04/04/95	Kaesz et al.			
	E	5,440,173	08/08/95	Evans, Jr. et al.			
	F	5,789,320	08/04/98	Andricacos et al.			
	G	5,807,788	09/15/98	Brodsky et al.			
BT	H	5,824,563	10/20/98	Hwang			
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	NO
BT	J	198 48 444 A1	12/23/99	Germany				X
BT	K	0 567 878 A1	11/03/93	Europe			X	
	L							
	M							
	N							

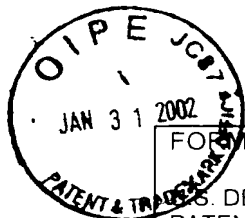
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

BT	O	Ziling Xue et al.: "Organometallic Chemical Vapor Deposition of Platinum Reaction Kinetics and Vapor Pressures of Precursors", Chem. Mater. 1992, No. 4, pp. 162-166
BT	P	Ju-Hong Kwon et al.: "Preparation of Pt thin films deposited by metalorganic chemical vapor deposition for ferroelectric thin films", Thin Solid Films, Vol. 3, 1997, pp. 136-142

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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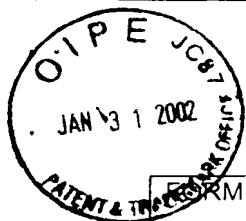
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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

BT	O	Tomonori Aoyama et al.: "Chemical Vapor Deposition of Ru and Its Application in (Ba, Sr)TiO ₃ Capacitors for Future DRAM", International Conference on Solid State Devices and Materials, Japan Society of Applied Physics, Tokyo, September 1998, pp. 44-45
BT	P	B.S. Kwak et al.: "Study of epitaxial platinum thin films grown by metalorganic chemical vapor deposition", Journal of Applied Physics, October 15, 1992, Vol. 72, No. 8, pp. 3735-3740

EXAMINER B. Talbot	DATE CONSIDERED 6/2/03
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	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>BT</i>	O	Alfred A. Zinn et al.: "Metal CVD", chapter 7, "Chemical Vapor Deposition of Platinum, Palladium and Nickel", VCH-Weinheim, 1994, pp. 329-355
	P	

EXAMINER <i>B. T. Carter</i>	DATE CONSIDERED <i>6/2/03</i>
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